

NS6130-10-1268

GALLIUM NITRIDE

on Sapphire Wafer

Quick Facts

Product	:	Gallium Nitride on Sapphire Wafer
Stock No	:	NS6130-10-1268
CAS	:	25617-97-4
Purity	:	>99.9%
Type	:	N Type

Technical Specification

Diameter	Thickness	Thickness of Sapphire
4"	4 $\mu\text{m} \pm 1\mu\text{m}$	650 $\pm 25\mu\text{m}$ for 4 inch

Gallium nitride on sapphire (GaN on Sapphire) is a popular material system used in the production of various electronic and optoelectronic devices. GaN and sapphire results in a highly efficient material system that is widely used in the production of high-power electronic devices, such as power transistors and high-frequency amplifiers, as well as in the production of high-brightness light-emitting diodes (LEDs) and laser diodes. GaN on Sapphire wafers are used in the production of RF devices, such as amplifiers and transistors.



* This image is for graphic purposes only and does not represent the actual product.

